

PROCEEDINGS OF THE
NINTH INTERNATIONAL CONFERENCE ON

CHEMICAL VAPOR DEPOSITION
1984

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NINTH INTERNATIONAL CONFERENCE ON

CHEMICAL VAPOR DEPOSITION 1984

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**HIGH TEMPERATURE MATERIALS,
ELECTRONICS, AND DIELECTRICS AND INSULATION DIVISIONS**

Proceedings Volume 84-6

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PREFACE

This volume is the Proceedings of the Ninth International Conference on Chemical Vapor Deposition (CVD-IX), held May 7-10, 1984 in Cincinnati, Ohio, U.S.A., as part of the Spring Meeting of The Electrochemical Society.

The number of papers published here, and the geographical distribution represented, attest to the continued worldwide vitality CVD:

| | |
|-------------------------|----|
| Denmark | 1 |
| Federal Rep. of Germany | 4 |
| Japan | 2 |
| Korea | 2 |
| Sweden | 3 |
| West Germany | 4 |
| France | 6 |
| United Kingdom | 1 |
| United States | 34 |
| USSR | 1 |

Sixty-two papers were scheduled for presentation at the conference. Of those, 58 are represented by full length manuscripts in these Proceedings. Recently about 500 CVD papers have been published each year (see, for example, "Chemical Vapor Deposition, 1960-1980, A Bibliography", Ed. D. T. Hawkins, IFI/Plenum, N.Y. 1981). This volume therefore contains about 10% of the CVD papers that will appear this year.

We thank the authors who worked hard and patiently preparing camera-ready copy for this publication. Publication of a proceedings at the time of the conference places extra demands on the everyone because of the early deadlines. The papers were reviewed by the session chairmen and by other reviewers whom they selected. Where necessary, papers were returned to the authors for revision. In general the process of review and revision went smoothly, especially considering the demands of communicating and sending manuscripts across international boundaries. Our thanks to authors and reviewers for the superior cooperation.

The topics of these papers reflect most of the current trends in CVD. It is gratifying to see continuing progress in fundamentals: heat and mass transport, chemical kinetics and thermodynamics. Several papers address the continuing concern for defect reduction and dopant control in single crystal CVD films. Others reflect an increased interest in low temperature processing, using plasma and photon-enhanced CVD. The materials represented in these Proceedings cover most of those to which CVD is being applied: silicon, germanium, III-V and II-VI semiconductors, metals, silicides, superconductors, magnetic and optical materials, and hard and protective coatings.

We would like to express our thanks to the many people who contributed to this volume, especially to the session chairmen who took on the major responsibility for reviewing the manuscripts and communicating with the authors, Sarah Kilfoyle, Electrochemical Society Publications Editor, who was a valuable and continuing source of information and support, and Christina Sampson, who capably managed the details of assembling the manuscripts into the final volume.

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February, 1984

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CONTENTS

| | |
|---|-----|
| PREFACE | iii |
| CONFERENCE ORGANIZATION | v |
| PART IA FUNDAMENTALS | |
| 1. "Modelling of Chemical Vapor Deposition Reactors", K. F. Jensen (Invited) | 3 |
| 2. "Fluid Mechanical Model for CVD in a Horizontal RF Reactor", J. C. Gillis, M. L. Hammond, and C. L. Ramiller | 21 |
| 3. "A Mathematical Model of Silicon Chemical Vapor Deposition", M. E. Coltrin, R. J. Kee, and J. A. Miller | 31 |
| 4. "In Situ Laser Measurements of Silicon CVD", W. G. Breiland, and P. Ho | 44 |
| 5. "Theoretical Description of CVD Processes", G. Wahl | 60 |
| PART IB FUNDAMENTALS | |
| 1. "Thermochemical Modeling of Steady State CVD Processes", K. E. Spear (Invited) | 81 |
| 2. "Experimental and Thermodynamic Investigations of the V-Si-H-Cl CVD System", M. S. Wang, and K. E. Spear | 98 |
| 3. "Analysis of Multicomponent LPCVD Processes, In Situ Doping of Polycrystalline Silicon", K. Roenigk, and K. F. Jensen | 112 |
| 4. "Autodoping and Introduction of Substrate Atoms into the Film During Chemical Vapor Deposition", J. Carlsson, and M. Boman | 129 |

Contents (Continued)

| | | |
|---|--|-----|
| 5. | "The Influence of the Reactivity of the Substrate on Grain Size and Adhesion of CVD Films", M. Boman and J. Carlsson | 150 |
| 6. | "A New CVD Method in a Closed Tube with a Three Zone Arrangement. Thermodynamics and Kinetics of Transport and Epitaxy for Semi Conducting Materials", F. Langlais and J. C. Launay | 165 |
| 7. | "Influence of Growth Temperature on the Physical Properties of Si Film on Yttria-Stabilized, Cubic Zirconia Substrates", A. L. Lin, and I. Golecki | 175 |
| PART II CVD FOR SILICON PROCESSING TECHNOLOGY | | |
| 1. | "Plasma Enhanced CVD", H. Y. Kumagai (Invited) | 189 |
| 2. | "Plasma Enhanced Chemical Vapor Deposition of TaSi ₂ ", K. Hieber, M. Stolz, and C. Wieczorek | 205 |
| 3. | "Optical Emission Spectroscopic Study of Silicon Nitride and Oxynitride Plasma Deposition Glow Discharge", V. S. Nguyen | 213 |
| 4. | "Nucleation and Growth of Al ₂ O ₃ on Si in the CVD Process", S. W. Choi, C. Kim, J. G. Kim, and J. S. Chun | 233 |
| 5. | "Photo-CVD for VLSI Isolation", J. Y. Chen, R. C. Henderson, J. T. Hall, and J. W. Peters (Invited) | 242 |
| 6. | "Characterization of LPCVD Aluminum for VLSI Processing", R. A. Levy, M. L. Green, and P. K. Gallagher (Invited) | 258 |
| 7. | "Deposition Parameters and Properties of Low Pressure Chemical Vapor Deposited Tungsten Silicide for Integrated Circuits Manufacture", K. A. Monnig, D. L. Brors, J. A. Fair, and K. C. Saraswat | 275 |

Contents (Continued)

| | | |
|-----|--|-----|
| 8. | "In-Situ Doped Silicon Via LPCVD; Interactions of the Dopant/Silane/Silicon Surface System", B. S. Meyerson and M. L. Yu | 287 |
| 9. | "Fabrication of Heavily Doped Si by PH ₃ /SiH ₄ Epitaxy", J. del Alamo, and R. Swanson | 295 |
| 10. | "Large-Area Epitaxial Growth of Chalcogen-Doped Silicon", C. Holm and E. Sirtl | 303 |

PART III SILICON EPITAXY FOR VLSI

| | | |
|----|---|-----|
| 1. | "Physical Defects in Silicon Vapor Phase Epitaxy", H. R. Chang, and B. J. Baliga (Invited) | 315 |
| 2. | "Influence of Epi-Substrate Material Properties on Getter Enhanced Epitaxial Processing Applied to CMOS and Bipolar Technologies", J. O. Borland, I. Bell, and R. Schindler | 324 |
| 3. | "N ⁺ and P ⁺ Substrate Effects on Epitaxial Silicon Properties", W. Dyson, J. A. Rossi, L. G. Hellwig, and J. W. Moody | 338 |
| 4. | "Slip-Free Epitaxial Silicon Deposition in an Induction-Heated Vertical Reactor", J. McDiarmid, L. H. Lawrence, and M. L. Hammond | 351 |

Contents (Continued)

PART IV EPITAXIAL AND POLYCRYSTALLINE SILICON FOR VLSI

- | | |
|--|-----|
| 1. "Plasma Enhanced Chemical Vapor Deposition of Silicon Epitaxial Layers, R. Reif (Invited) | 359 |
| 2. "A Near Future Perspective on Silicon Epitaxy", W. Benzing (Invited) | 373 |
| 3. "Economics of Epitaxial Silicon Production", M. L. Hammond | 380 |
| 4. "CVD Epitaxial Autodoping in BiPolar VLSI Technology", G. R. Srinivasan (Invited) | 387 |
| 5. "LPCVD Polycrystalline Silicon: Properties of Doped and Undoped Films Prepared Via the Amorphous Phase", M. T. Duffy, and G. Harbeke (Invited) | 400 |
| 6. "Autodoping of Boron Doped Epitaxial Layers for C-MOS Devices", W. C. Metz | 420 |
| 7. "Pattern Distortion During CVD Epitaxy on (100) Silicon at Atmospheric and Reduced Pressure", J. F. Corboy, G. W. Cullen, and R. H. Pagliaro, Jr. | 434 |
| 8. "Reduced Pressure Silicon Epitaxy in an Induction-Heated Vertical Reactor", L. H. Lawrence, J. McDiarmid, and M. L. Hammond | 454 |
| 9. "Effect of Substrate Preparation and Growth Ambient on Silicon Selective Epitaxy", H. M. Liaw, D. Weston, B. Reuss, M. Birrittella, and J. Rose | 463 |

PART V CVD OF COMPOUND SEMICONDUCTORS AND OPTICAL MATERIALS

- | | |
|--|-----|
| 1. "Preparation of Optical Fibres by Means of the PCVD Process", P. Geittner (Invited) | 479 |
|--|-----|

Contents (Continued)

| | | |
|--|--|-----|
| 2. | "Chemical Vapor Deposition for III-V Compound Semiconductor Devices", R. D. Dupuis (Invited) | 503 |
| 3. | "Chemical Vapor Deposition of Samarium Chalcogenides from Organometallic Starting Compounds", P. D. Hillman, A. L. Phillips, M. R. Jacobson, and U. J. Gibson | 517 |
| 4. | "The Mechanical Properties of CVD-Grown Zinc Sulphide and their Dependence on the Conditions of Growth", K. L. Lewis, A. M. Pitt, J. A. Savage, J. E. Field, and D. Townsend | 530 |
| 5. | "CVD Amorphous Germanium: Preparation and Properties", D. D. Allred, and J. A. Piontkowski | 546 |
| PART VI CVD OF REFRACTORY MATERIALS AND COATINGS | | |
| 1. | "Vapodeposition of Si ₃ N ₄ from Si(CH ₃) ₄ -/NH ₃ Mixtures Under Low Pressure, J. F. Lartigue, M. Ducarroir, and B. Armas | 561 |
| 2. | "High-resolution Electron Microscopy of Grain Boundaries in Chemical Vapour Deposited Si ₃ N ₄ and SiC", H. Hiraga, M. Hirabayashi, K. Niihara, and T. Hirai | 575 |
| 3. | "High Temperature X-Ray Diffraction Study of CVD Si ₃ N ₄ ", J. F. Lartigue, and F. Sibieude | 583 |
| 4. | "A Tentative Modelization of Titanium Carbide C.V.I. Within the Pore Network of Two-Dimensional Carbon-Carbon Composite Preforms", J. Y. Rossignol, F. Langlais, and R. Naslain | 596 |
| 5. | "Thermodynamics of the Zr-C System - Calculated Equilibrium Phase Diagram and Phase Diagram for Deposition from a CH ₄ -ZrCl ₄ -H ₂ Gaseous Mixture", P. Salles, M. Ducarroir, and C. Bernard | 615 |

Contents (Continued)

| | | |
|-----|--|-----|
| 6. | "Deposition of Boron from $\text{BCl}_3/\text{H}_2/\text{N}_2$ - Gas Mixtures on Steels with Low Alloy Content", L. Singheiser, G. Wahl, and F. Hegewaldt | 625 |
| 7. | "Plasma Assisted Chemical Vapor Deposition of Boron", L. Vandenbulcke, and R. Herbin | 639 |
| 8. | "CVD of SiC -Interlayers and their Interaction with Carbon Fibers and with Multilayered NbN -Coatings", K. Brennfleck, E. Fitzer, G. Schoch, and M. Dietrich | 649 |
| 9. | "Preparation of Al -Stabilized Superconducting $\text{NbCl}_{1-x}\text{N}_x$ Carbon Fibers", F. Schmaderer, G. Wahl, M. Dietrich, and C. H. Dustman | 663 |
| 10. | "Heteroepitaxy of Ferrite-Spinel Layers by CVD-Method", L. N. Aleksandrov, L. A. Mitlina, V. V. Molchanov, and A. L. Vasilyev | 673 |

PART VII CVD OF HARD COATINGS

| | | |
|----|--|-----|
| 1. | "Preparation and Machining Properties of CVD Al_2O_3 Coated Cemented Carbide Tools with Various Intermediate Layers", J. Lindstrom, M. Collin, and A. Thelin | 689 |
| 2. | "Thickness Uniformity of CVD Al_2O_3 Coatings", W. A. Bryant, and D. B. Kropfl | 709 |
| 3. | "TEM Study of TiC and Alumina/ TiC Coatings on Cemented Carbides", S. Vuorinen | 719 |
| 4. | "Titanium Nitride Coating by Plasma CVD", N. Kikuchi, Y. Oosawa and A. Nishiyama | 728 |
| 5. | "Chemical Vapor Deposition of TiC Using Propane", D. S. Baik, M. S. Kim, and J. S. Chun | 745 |

Contents (Continued)

| | | |
|---------------|---|-----|
| 6. | "Compositional and Microhardness Profiles in CVD Coatings with a Ball Wear Scar Technique", P. K. Mehrotra, D. T. Quinto, and G. J. Wolfe | 757 |
| 7. | "C.V.D. Elaboration of Amorphous Thin Films by Co-Deposition of Nickel and Phosphine", R. Bourezg, R. Morancho, and G. Constant | 772 |
| 8. | "Chemical Vapor Deposition of Erosion-Resistant TiB ₂ Coatings", A. J. Caputo, W. J. Lackey, and I. G. Wright | 782 |
| AUTHOR INDEX | | 801 |
| KEYWORD INDEX | | 803 |

I. FUNDAMENTALS (A)

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MODELLING OF CHEMICAL VAPOR DEPOSITION REACTORS

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The modelling of chemical vapor deposition (CVD) reactors is reviewed with emphasis on reactors for growth of electronic materials. Fluid flow phenomena characteristic of CVD systems including free convection driven instabilities are described. The formulation of detailed species balances to account for the combined mass transfer and chemical kinetics are outlined. In addition, the development of kinetic rate expressions for CVD is discussed. The utility of CVD reactor analysis in extracting chemical kinetics from experimental deposition data is demonstrated for three particularly advantageous reaction configurations, (1) rotating disk, (2) stagnation point flow, and (3) impinging jet. Finally, the perceived future needs in CVD reactor modelling are outlined.

INTRODUCTION

Mathematical models for chemical vapor deposition (CVD) reactors relate performance variables (e.g. deposition rate and film composition) to operation conditions (e.g. reactor geometry, flow pattern, reactant concentration, and temperature profile). The model is formed by a complete and consistent set of mathematical equations which vary in complexity according to the level of detail sought in the representation. The simplest "model" is a statistical correlation of input parameters and performance variables. Such an approach is limited to a specific reactor at hand and a narrow operation region. It can neither be used to extrapolate the reactor performance to new operating conditions nor to design new reactors. Moreover, it provides little, if any, insight into the underlying physical and chemical rate processes.

CVD reactor models serve three main purposes, (i) the prediction of reactor performance for a given reactor and known chemical kinetics, (ii) the evaluation of kinetic parameters from reactor data, and (iii) the design of new reactors for a given process. (i) and (ii) have received the most attention in the CVD literature. Reactor design, to a large extent, has been limited to modification of existing configurations such as the horizontal and barrel geometries. In the following paragraphs, reactor models are reviewed with emphasis on reactors for deposition of elec-

tronic materials. Nevertheless, much of the discussion also applies to other CVD processes such as the deposition of protective coatings.

CVD REACTORS

Figure 1 illustrates conventional CVD reactors. In the horizontal, pancake, and barrel reactors the wall temperatures are usually considerably cooler than the deposition surfaces which are heated by rf coupling or quartz radiant heaters. The multiple-wafer-in-tube (or boat) reactor is a hot wall reactor where deposition also occurs on the reactor walls. The horizontal and barrel reactors are usually modelled in the same fashion since the flow geometry of the horizontal reactor is similar to that of one barrel side. However, the similarity is not present when the barrel is rotated as is often done in practice. Furthermore, buoyancy effects appear differently in the two reactors.

The Eversteijn model for horizontal reactors, the so-called stagnant layer model, is a well known exponent for the film theory modelling of horizontal reactors. Eversteijn et al. (1,2) considered a stagnant layer of fluid adjacent to the susceptor coupled with a well-mixed main flow region between the upper end of this layer and the reactor wall. The diffusion equation for transport across the stagnant layer was combined with a plug flow description of the main flow region to give the reactor model. The stagnant layer concept originated from flow visualization experiments with TiO_2 particles showing an almost particle free layer close to the susceptor which was interpreted as evidence for a stagnant layer. However, recent laser Doppler velocitimeter studies have revealed that the seed particles were driven away from the substrate by thermophoretic forces (3). Ban and Gilbert (4,5) used the same concept as Eversteijn but improved the model by considering a developing boundary layer and including thermodiffusion effects.

Several models have been based on fully developed laminar flow (6-9). However, as will be discussed in the next section, hydrodynamic and thermal entrance effects are significant in horizontal and barrel reactors. Consequently the applicability of the models is limited in reactor design and optimization. Nevertheless, they may serve a purpose in improving our understanding of the CVD processes. The most complete analysis of the barrel reactor so far appears to be given by Juza and Cernak (10). They make use of the 2D momentum, mass, and energy balances to demonstrate the development of the transverse velocity, concentration, and temperature profiles along the susceptor. Additional details of the reactor models may be found in (11) where key model assumptions are summarized for each model.

FLUID FLOW PHENOMENA IN CVD

The fluid flow has a pronounced influence on the performance of CVD reactors since the transport processes in the fluid phase regulate the